TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7WH125FU, TC7WH125FK

DUAL BUS BUFFER

The TC7WH125 is an advanced high speed CMOS DUAL BUS BUFFERS fabricated with silicon gate CMOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The require 3-state control input \overline{G} to be set high to place the output into the impedance.

This device is designed to be used with 3-state memory address drivers, etc.

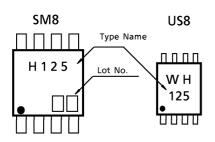
An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V system and two supply system such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

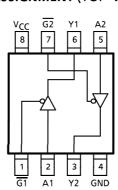
FEATURES

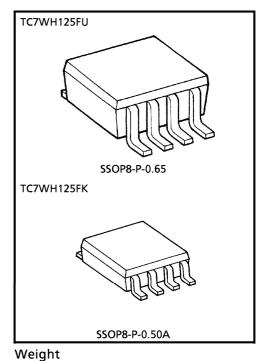
MARKING

- High Speed $t_{pd} = 3.8 \text{ns}$ (Typ.) at $V_{CC} = 5 \text{V}$
- Low Power Dissipation $I_{CC} = 2\mu A$ (Max.) at $Ta = 25^{\circ}C$
- High Noise Immunity V_{NIH} = V_{NIL} = 28%
 V_{CC} (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays $\cdots t_{pLH} = t_{pHL}$
- Wide Operation Voltage Range ··· V_{CC} (opr) = 2~5.5V
- Low Noise V_{OLP} = 0.8V (Max.)

PIN ASSIGNMENT (TOP VIEW)





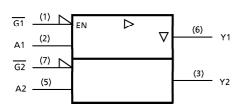


SSOP8-P-0.65 : 0.02g (Typ.) SSOP8-P-0.50A : 0.01g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Supply Voltage Range	Vcc	-0.5~7.0	V	
DC Input Voltage	VIN	-0.5~7.0	٧	
DC Output Voltage	Vout	-0.5~V _{CC} +0.5	٧	
Input Diode Current	lικ	- 20	mA	
Output Diode Current	^I ОК	± 20	mA	
DC Output Current	lout	± 25	mA	
DC V _{CC} /Ground Current	lcc	± 50	mA	
Bayyar Dissination	D-	300 (SM8)	\//	
Power Dissipation	PD	200 (US8)	mW	
Storage Temperature	T _{stg}	-65∼150	°C	
Lead Temperature (10 s)	TL	260	°C	

LOGIC DIAGRAM



TRUTH TABLE

INPUTS		OUTPUTS		
G	Α	Y		
Н	×	Z		
L	L	L		
L	Н	Н		

x : Don't Care Z : High Impedance

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	Vcc	2~5.5	V
Input Voltage	VIN	0~5.5	V
Output Voltage	Vout	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C
Input Rise and Fall Time	dt/dv	$0 \sim 100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{V)}$	ns / V
	ut/uv	$0\sim20 \ (V_{CC} = 5 \pm 0.5V)$	115/ V

DC ELECTRICAL CHARACTERISTICS

CLIADACTERISTIC	SYMBOL	TEST CONDITION		Vcc			C	Ta = -40~85°C		UNIT	
CHARACTERISTIC SYMBOL TEST CONDITION		V _C C (V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT			
High Lovel				2.0	1.5	_	_	1.5	_		
High-Level Input Voltage	VIH	_		3.0~ 5.5	V _C C ×0.7	-	_	V _{CC} ×0.7		٧	
Low-Level				2.0	_	_	0.5	_	0.5		
Input Voltage	V _{IL}	_		3.0~ 5.5	_	-	V _C C ×0.3		V _{CC} ×0.3	V	
		V _{IN} = V _{IH} or V _{IL}		2.0	1.9	2.0	_	1.9	_	V	
High-Level			$I_{OH} = -50\mu A$	3.0	2.9	3.0		2.9			
Output Voltage	VOH			4.5	4.4	4.5		4.4	_		
Output Voltage			$I_{OH} = -4mA$	3.0	2.58	1		2.48	1		
			$I_{OH} = -8mA$	4.5	3.94		_	3.8	1		
	V _{OL}	V _{IN} = V _{IL}	I _{OL} = 50μA	2.0	_	0.0	0.1	_	0.1		
Low-Level				3.0	_	0.0	0.1	_	0.1		
Output Voltage				4.5	_	0.0	0.1	_	0.1	V	
Catput Voltage			$I_{OL} = 4mA$	3.0	_	_	0.36	_	0.44		
			$I_{OL} = 8mA$	4.5	_	_	0.36	_	0.44		
3-State Output Off-State Current	loz	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		5.5		_	± 0.25	_	± 2.5	μ A	
Input Leakage Current	IN	V _{IN} = V _{CC} or GND		0~ 5.5			± 0.1		± 1.0	μΑ	
Quiescent Supply Current	Icc	V _{IN} = V _{CC} or GND		5.5	_	_	2.0	_	20.0	μ A	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$)

CHADACTERISTIC	SYMBOL	TEST CONDITION V _{CC} (V) C _L (pF)		Ta = 25°C			Ta = -40~85°C		LINUT	
CHARACTERISTIC	STIVIBOL			C _L (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Propagation Delay			3.3 ± 0.3	15	_	5.6	8.0	1.0	9.5	
	^t pLH			50	_	8.1	11.5	1.0	13.0	
Time	t _{pHL}		5.0 ± 0.5	15	_	3.8	5.5	1.0	6.5	ns
	•		3.0 ± 0.3	50	_	5.3	7.5	1.0	8.5	
		$R_L = 1k\Omega$	3.3 ± 0.3	15	_	5.4	8.0	1.0	9.5	- ns
3-State Output	tpZL			50	_	7.9	11.5	1.0	13.0	
Enable Time	^t pZL ^t pZH		5.0 ± 0.5	15	_	3.6	5.1	1.0	6.0	
				50	_	5.1	7.1	1.0	8.0	
3-State Output	^t pLZ	D. 1k()	3.3 ± 0.3	50	_	9.5	13.2	1.0	15.0	ns
Disable Time	t _{pHZ}	$R_L = 1k\Omega$	5.0 ± 0.5	50	_	6.1	8.8	1.0	10.0	ns
Output to Output	tosLH	(Note 1)	3.3 ± 0.3	50	_	_	1.5	_	1.5	nc
Skew	tosHL	(Note 1)	5.0 ± 0.5	50	_	_	1.0	_	1.0	ns
Input Capacitance	CIN				_	4	10	_	10	рF
Output Capacitance	COUT				_	6	_	_	_	рF
Power Dissipation Capacitance (Note 2)	C _{PD}				_	14	_	_	_	pF

(Note 1) : Parameter guaranteed by design. $t_{OSLH} = |t_{pLHm} - t_{pLHn}| \setminus t_{OSHL} = |t_{pHLm} - t_{pHLn}|$ (Note 2) : CPD is defined as the value of the internal equivalent capacitance which is

calculated from the operating current consumption without load. Average operating current can be obtained by the equation :

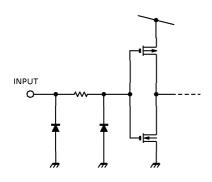
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2$ (per bit)

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NOISE CHARACTERISTICS (Ta = 25°C, Input $t_r = t_f = 3ns$)

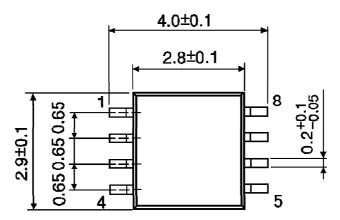
CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{CC} (V)	TYP.	LIMIT	UNIT
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	C _L = 50pF	5.0	0.3	0.8	٧
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	C _L = 50pF	5.0	-0.3	-0.8	V
Minimum High Level Dynamic Input Voltage	V _{IHD}	C _L = 50pF	5.0	_	3.5	V
Maximum Low Level Dynamic Input Voltage	V _{ILD}	C _L = 50pF	5.0		1.5	V

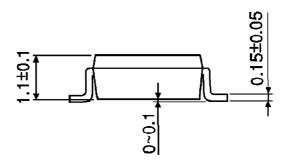
INPUT EQUIVALENT CIRCUIT



PACKAGE DIMENSIONS

SSOP8-P-0.65 Unit: mm

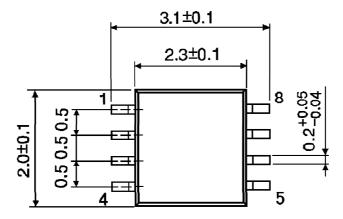


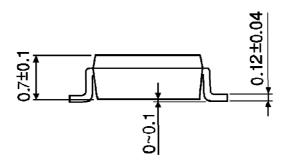


Weight: 0.02g (Typ.)

PACKAGE DIMENSIONS

SSOP8-P-0.50A Unit: mm





Weight: 0.01g (Typ.)

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